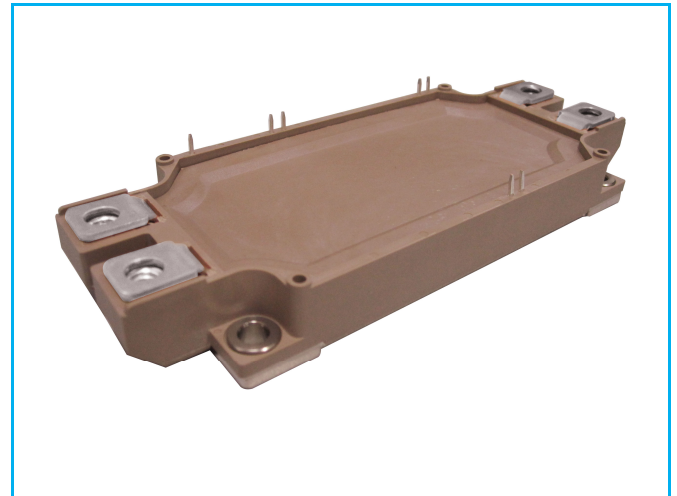


PRODUCT FEATURES

- 650V IGBT³ CHIP(Trench+Field Stop technology)
- Low saturation voltage and positive temperature coefficient
- Low switching losses and short tail current
- Free wheeling diodes with fast and soft reverse recovery
- Temperature sense included

APPLICATIONS

- 3-Level applications



IGBT

ABSOLUTE MAXIMUM RATINGS($T_C=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions	Values	Unit
V_{CES}	Collector Emitter Voltage	$T_J=25^{\circ}\text{C}$	V
V_{GES}	Gate Emitter Voltage		
I_C	DC Collector Current	$T_C=25^{\circ}\text{C}, T_{Jmax}=175^{\circ}\text{C}$	710
		$T_C=60^{\circ}\text{C}, T_{Jmax}=175^{\circ}\text{C}$	600
I_{CM}	Repetitive Peak Collector Current	$t_p=1\text{ms}$	1200
P_{tot}	Power Dissipation Per IGBT	$T_C=25^{\circ}\text{C}, T_{Jmax}=175^{\circ}\text{C}$	1760

Diode

ABSOLUTE MAXIMUM RATINGS ($T_C=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions	Values	Unit
V_{RRM}	Repetitive Reverse Voltage	$T_J=25^{\circ}\text{C}$	V
$I_{F(AV)}$	Average Forward Current		A
I_{FRM}	Repetitive Peak Forward Current	$t_p=1\text{ms}$	
I^2t		$T_J=125^{\circ}\text{C}, t=10\text{ms}, V_R=0\text{V}$	KA ² S

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MMG600WB065TLB6EN

IGBT

ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions		Min.	Typ.	Max.	Unit
$V_{GE(th)}$	Gate Emitter Threshold Voltage	$V_{CE}=V_{GE}, I_C=9.6\text{mA}$	4.9	5.8	6.5	V
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$I_C=600\text{A}, V_{GE}=15\text{V}, T_J=25^\circ\text{C}$		1.45	1.9	
		$I_C=600\text{A}, V_{GE}=15\text{V}, T_J=125^\circ\text{C}$		1.6		
		$I_C=600\text{A}, V_{GE}=15\text{V}, T_J=150^\circ\text{C}$		1.7		
I_{CES}	Collector Leakage Current	$V_{CE}=650\text{V}, V_{GE}=0\text{V}, T_J=25^\circ\text{C}$			1	mA
		$V_{CE}=650\text{V}, V_{GE}=0\text{V}, T_J=150^\circ\text{C}$			5	mA
I_{GES}	Gate Leakage Current	$V_{CE}=0\text{V}, V_{GE}=\pm 15\text{V}, T_J=25^\circ\text{C}$	-600		600	nA
R_{gint}	Integrated Gate Resistor			0.7		Ω
Q_g	Gate Charge	$V_{CE}=300\text{V}, I_C=600\text{A}, V_{GE}=\pm 15\text{V}$		6.5		μC
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}, V_{GE}=0\text{V}, f=1\text{MHz}$		39		nF
C_{res}	Reverse Transfer Capacitance				1.15	
$t_{d(on)}$	Turn on Delay Time	$V_{CC}=300\text{V}, I_C=600\text{A}$ $R_G=1.7\Omega,$ $V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=25^\circ\text{C}$		120	ns
			$T_J=150^\circ\text{C}$		140	ns
t_r	Rise Time	$V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=25^\circ\text{C}$		110	ns
			$T_J=150^\circ\text{C}$		120	ns
$t_{d(off)}$	Turn off Delay Time	$V_{CC}=300\text{V}, I_C=600\text{A}$ $R_G=1.7\Omega,$ $V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=25^\circ\text{C}$		500	ns
			$T_J=150^\circ\text{C}$		560	ns
t_f	Fall Time	$V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=25^\circ\text{C}$		70	ns
			$T_J=150^\circ\text{C}$		90	ns
E_{on}	Turn on Energy	$V_{CC}=300\text{V}, I_C=600\text{A}$ $R_G=1.7\Omega,$ $V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=25^\circ\text{C}$		5	mJ
			$T_J=125^\circ\text{C}$		6	mJ
			$T_J=150^\circ\text{C}$		6.5	mJ
E_{off}	Turn off Energy	$V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=25^\circ\text{C}$		24	mJ
			$T_J=125^\circ\text{C}$		27.5	mJ
			$T_J=150^\circ\text{C}$		28.5	mJ
I_{SC}	Short Circuit Current	$tpsc \leq 6\mu\text{s}, V_{GE}=15\text{V}$ $T_J=150^\circ\text{C}, V_{CC}=360\text{V}$		3000		A
R_{thJC}	Junction to Case Thermal Resistance (Per IGBT)				0.085	K/W

Diode

ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions		Min.	Typ.	Max.	Unit
V_F	Forward Voltage	$I_F=600\text{A}, V_{GE}=0\text{V}, T_J=25^\circ\text{C}$		1.55	1.95	V
		$I_F=600\text{A}, V_{GE}=0\text{V}, T_J=125^\circ\text{C}$		1.50		
		$I_F=600\text{A}, V_{GE}=0\text{V}, T_J=150^\circ\text{C}$		1.45		
t_{rr}	Reverse Recovery Time	$I_F=600\text{A}, V_R=300\text{V}$ $dI_F/dt=-5000\text{A}/\mu\text{s}$ $T_J=150^\circ\text{C}$		450		ns
I_{RRM}	Max. Reverse Recovery Current			300		A
Q_{RR}	Reverse Recovery Charge			47		μC
E_{rec}	Reverse Recovery Energy			12.6		mJ
R_{thJCD}	Junction to Case Thermal Resistance (Per Diode)				0.15	K/W

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NTC CHARACTERISTICS ($T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions	Min.	Typ.	Max.	Unit
R_{25}	Resistance $T_C=25^\circ\text{C}$		5		K Ω
$B_{25/50}$	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298.15 \text{ K}))]$		3375		K

MODULE CHARACTERISTICS ($T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions	Values	Unit	
T_{Jmax}	Max. Junction Temperature	175	°C	
T_{Jop}	Operating Temperature	-40~150		
T_{stg}	Storage Temperature	-40~125		
V_{isol}	Isolation Breakdown Voltage	AC, 50Hz(R.M.S), t=1minute	3000	V
CTI	Comparative Tracking Index		> 225	
Torque	to heatsink	Recommended (M5)	2.5~5	Nm
	to terminal	Recommended (M6)	3~5	Nm
Weight			350	g

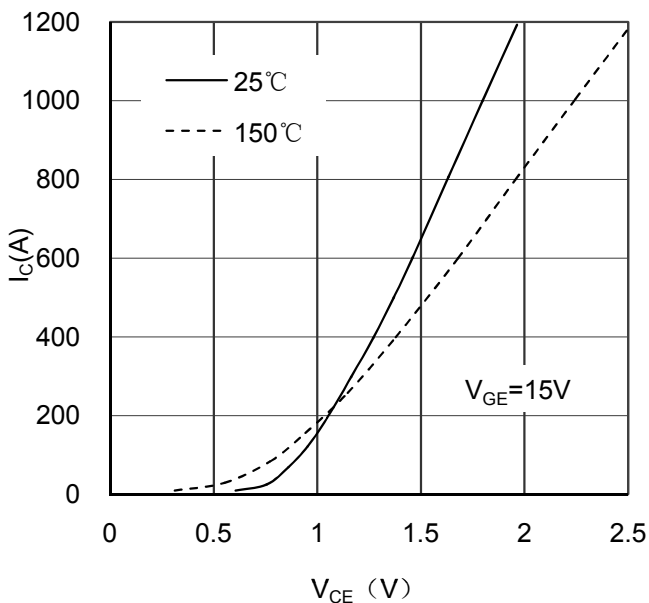


Figure 1. Typical Output Characteristics IGBT

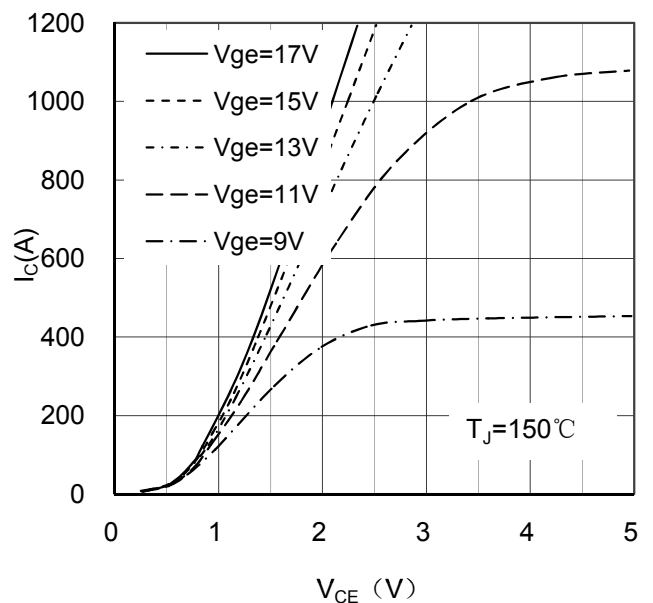


Figure 2. Typical Output Characteristics IGBT

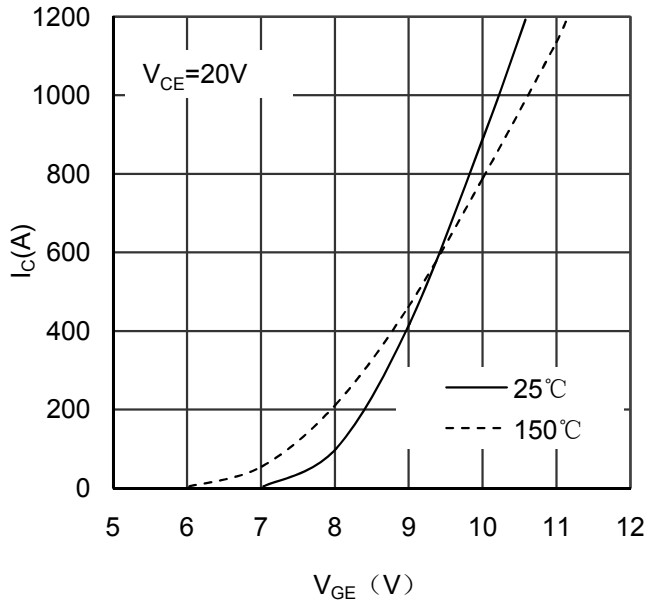


Figure 3. Typical Transfer characteristics IGBT

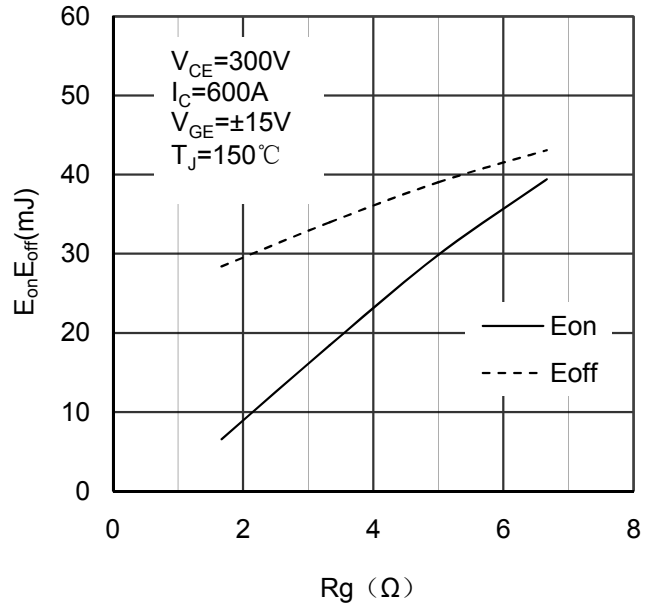


Figure 4. Switching Energy vs Gate Resistor IGBT

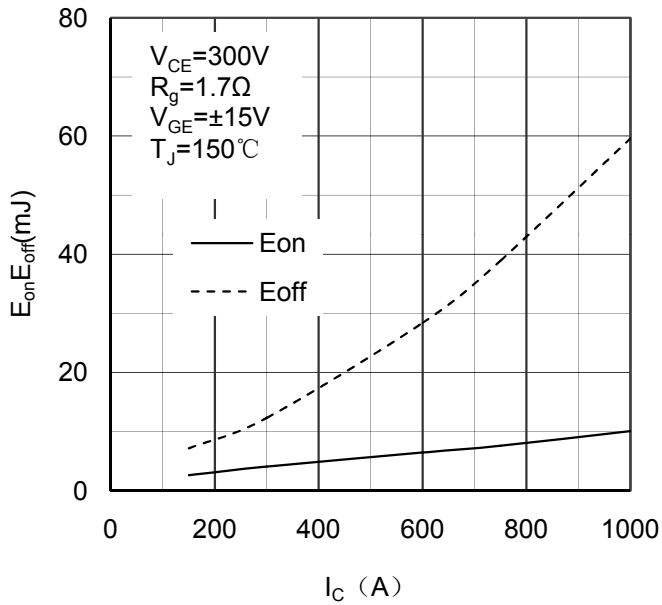


Figure 5. Switching Energy vs Collector Current IGBT

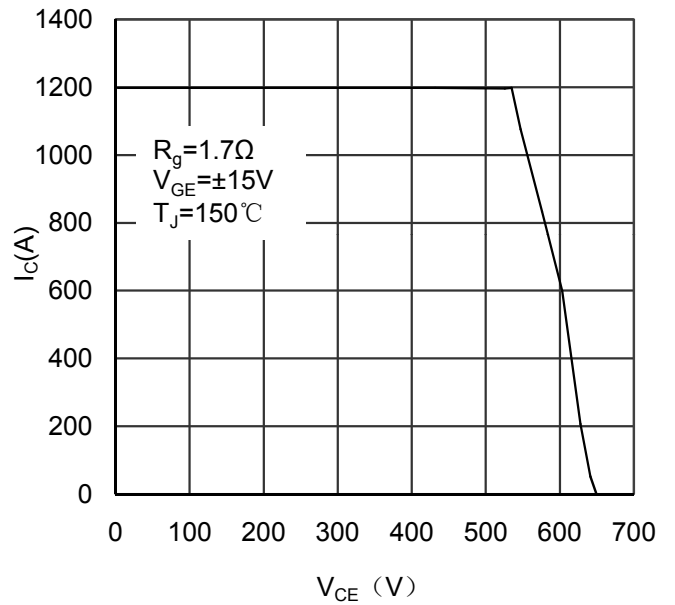


Figure 6. Reverse Biased Safe Operating Area IGBT

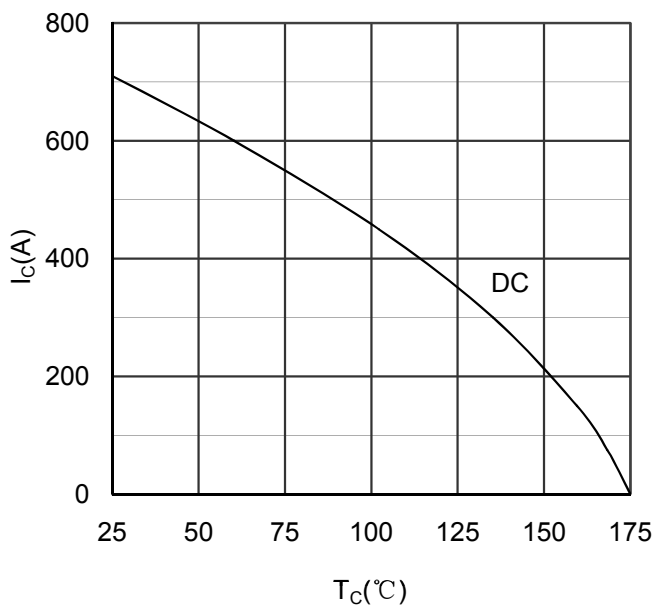


Figure 7. Collector Current vs Case temperature IGBT

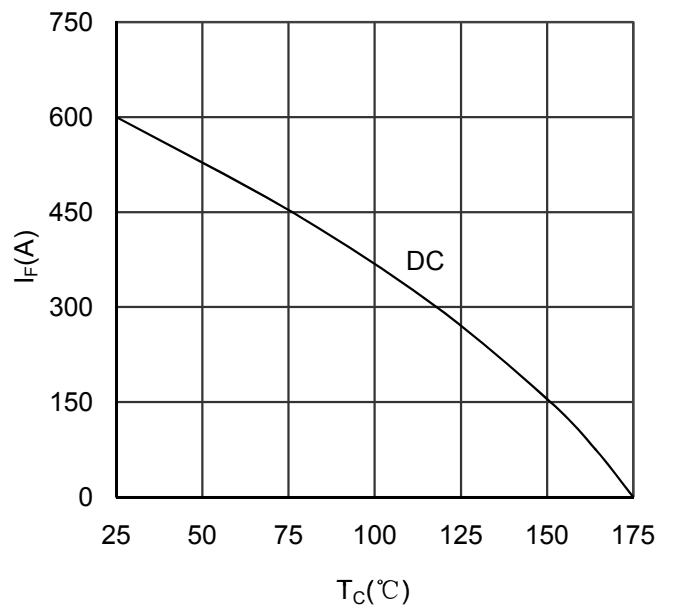


Figure 8. Forward current vs Case temperature Diode

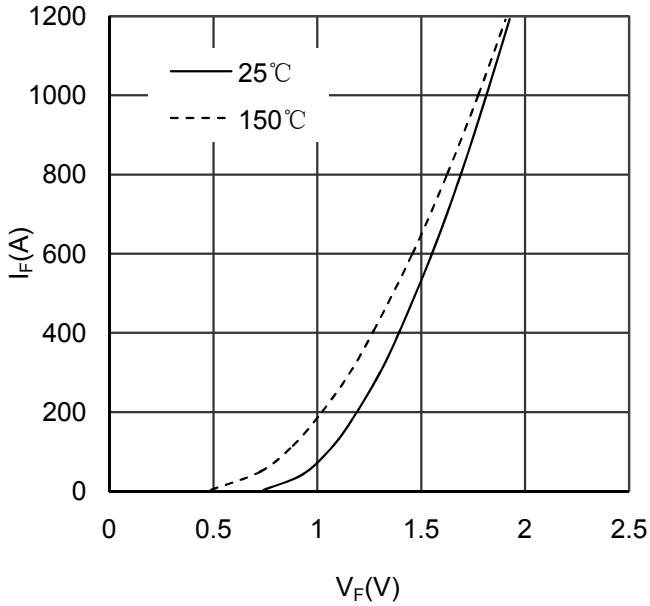


Figure 9. Diode Forward Characteristics Diode

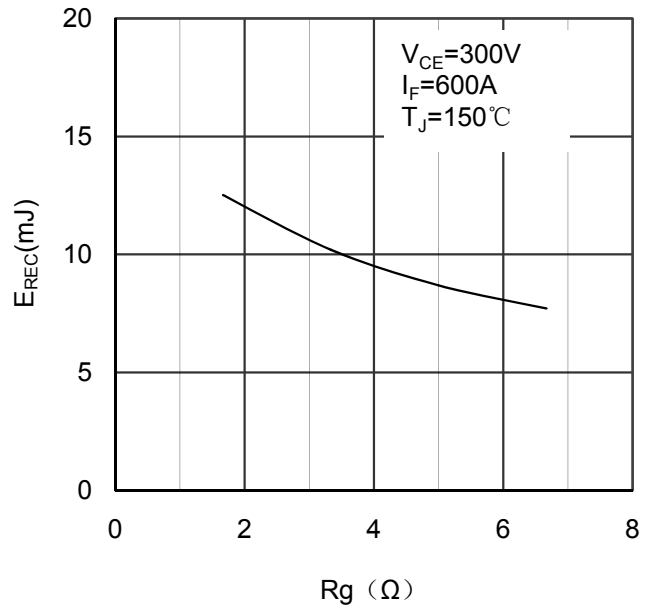


Figure 10. Switching Energy vs Gate Resistor Diode

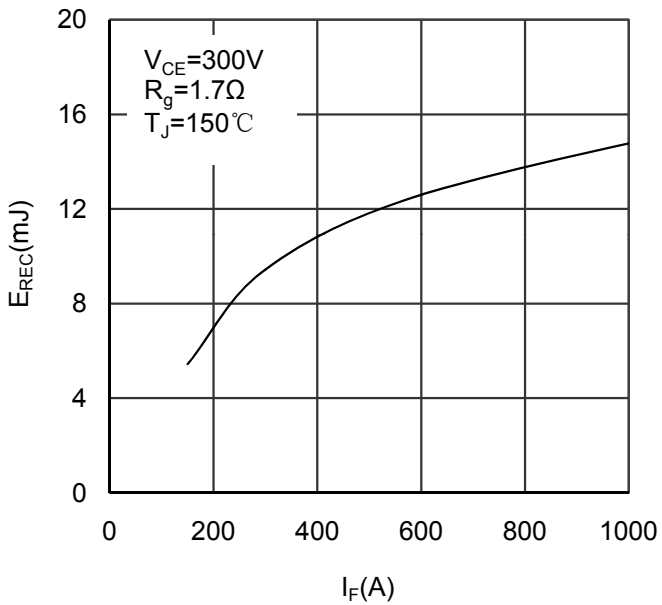


Figure 11. Switching Energy vs Forward Current Diode

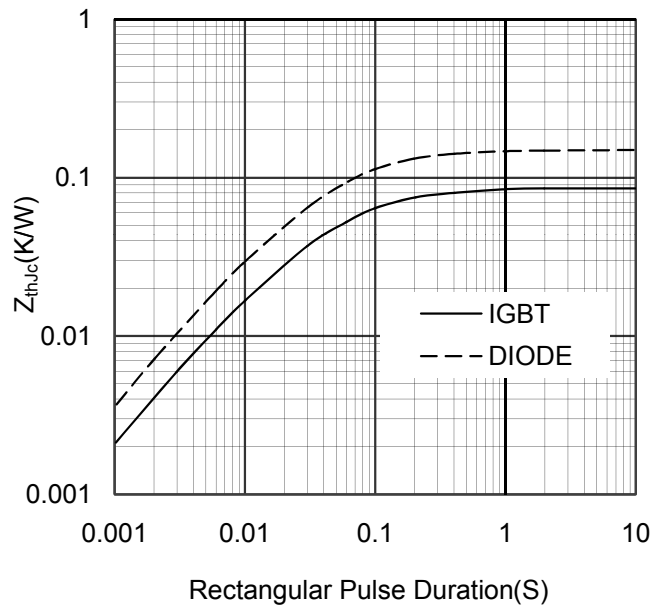


Figure 12. Transient Thermal Impedance of Diode and IGBT

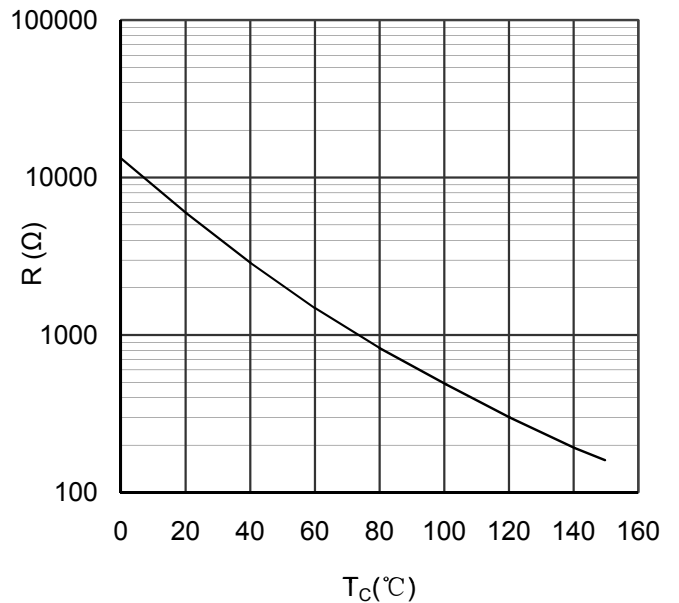


Figure 13. NTC Characteristics

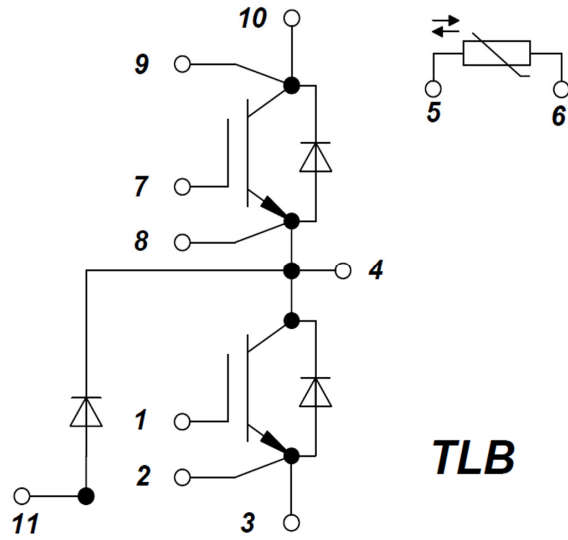
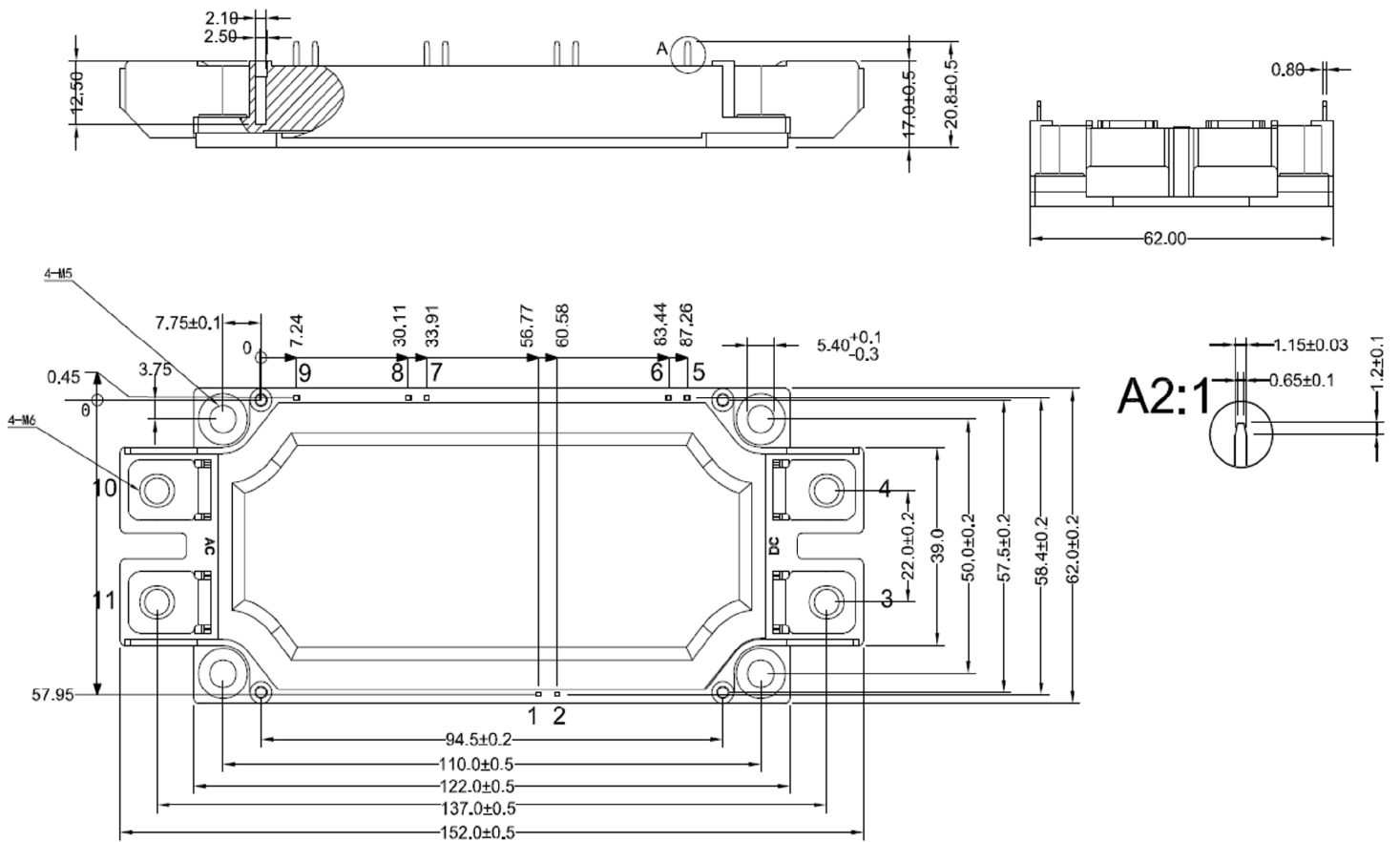


Figure 14. Circuit Diagram



Dimensions in (mm)

Figure 15. Package Outline